

Friedrich-Leonhard Schein

List of Publications by Year in descending order

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18
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687363

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19
docs citations

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times ranked

1239
citing authors

#	ARTICLE	IF	CITATIONS
1	Process Modules for High-Density Interconnects in Panel-Level Packaging. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2020, 10, 5-10.	2.5	5
2	High Density Fan-Out Panel Level Packaging of Multiple Dies Embedded in IC Substrates. , 2019, , .		0
3	High Density Interconnect Processes for Panel Level Packaging. , 2018, , .		6
4	Oxide bipolar electronics: materials, devices and circuits. Journal Physics D: Applied Physics, 2016, 49, 213001.	2.8	83
5	Room-temperature Domain-epitaxy of Copper Iodide Thin Films for Transparent CuI/ZnO Heterojunctions with High Rectification Ratios Larger than 109. Scientific Reports, 2016, 6, 21937.	3.3	91
6	All-Oxide Inverters Based on ZnO Channel JFETs With Amorphous ZnCo ₂ O ₄ . IEEE Transactions on Electron Devices, 2015, 62, 4004-4008.	3.0	15
7	All Amorphous Oxide Bipolar Heterojunction Diodes from Abundant Metals. Advanced Electronic Materials, 2015, 1, 1400023.	5.1	45
8	Highly rectifying p-ZnCo ₂ O ₄ /n-ZnO heterojunction diodes. Applied Physics Letters, 2014, 104, 022104.	3.3	45
9	Cuprous iodide - a p-type transparent semiconductor: history and novel applications. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1671-1703.	1.8	178
10	Transparent p-CuI/n-ZnO heterojunction diodes. Applied Physics Letters, 2013, 102, .	3.3	135
11	Comparison of ZnO-Based JFET, MESFET, and MISFET. IEEE Transactions on Electron Devices, 2013, 60, 1828-1833.	3.0	22
12	Cuprous iodide - a p-type transparent semiconductor: history and novel applications (Phys. Status) Tj ETQq0 0 0 rgBT/Overlock 10 Tf 50	1.8	90
13	ZnO-Based n-Channel Junction Field-Effect Transistor With Room-Temperature-Fabricated Amorphous p-Type ZnCo_2O_4 Gate. IEEE Electron Device Letters, 2012, 33, 676-678.	3.9	28
14	Light and Temperature Stability of Fully Transparent ZnO-Based Inverter Circuits. IEEE Electron Device Letters, 2011, 32, 515-517.	3.9	3
15	Recent Progress on ZnO-Based Metal-Semiconductor Field-Effect Transistors and Their Application in Transparent Integrated Circuits. Advanced Materials, 2010, 22, 5332-5349.	21.0	140
16	Transparent semiconducting oxides: materials and devices. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1437-1449.	1.8	129
17	High-gain integrated inverters based on ZnO metal-semiconductor field-effect transistor technology. Applied Physics Letters, 2010, 96, 113502.	3.3	21
18	Several Approaches to Bipolar Oxide Diodes with High Rectification. Advances in Science and Technology, 0, , .	0.2	11